



GP2M023A050N Information

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For Reference Only

Part Number GP2M023A050N

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 23A TO3PN

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP2M023A050N Specifications

Manufacturer Part Number GP2M023A050N Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 64nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3270pF @ 25V Vgs (Max) ± 30V FET Feature - Power Dissipation (Max) 347W (Tc) Rds On (Max) @ Id, Vgs 220 mOhm @ 11.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series - FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 30V ### 347W (Tc) Rds On (Max) @ Id, Vgs Operating Temperature ### 450°C ### 470°C (TJ) Mounting Type Supplier Device Package TO-3P-3, SC-65-3	Manufacturer Part Number	GP2M023A050N
Package TO-3P-3, SC-65-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 64nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3270pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 347W (Tc) Rds On (Max) @ Id, Vgs 220 mOhm @ 11.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Manufacturer	Global Power Technologies Group
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	Package	TO-3P-3, SC-65-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs64nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3270pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	23A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jemperature Jemperatur	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 220 mOhm @ 11.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)347W (Tc)Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	64nC @ 10V
FET Feature - Power Dissipation (Max) 347W (Tc) Rds On (Max) @ Id, Vgs 220 mOhm @ 11.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Input Capacitance (Ciss) (Max) @ Vds	3270pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 220 mOhm @ 11.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs220 mOhm @ 11.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PNPackage / CaseTO-3P-3, SC-65-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Power Dissipation (Max)	347W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	220 mOhm @ 11.5A, 10V
Supplier Device Package TO-3PN Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3PN
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

GP2M023A050N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M023A050N Payment Methods





















GP2M023A050N Shipping Methods













If you have any question about GP2M023A050N, please do not hesitate to contact us!

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